

# 10V Drive Nch MOSFET

## R4008AND

● **Structure**

Silicon N-channel MOSFET

● **Features**

- 1) Low on-resistance.
- 2) High-speed switching.
- 3) Wide SOA.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

● **Application**

Switching

● **Packaging specifications**

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
R4008AND		○

● **Absolute maximum ratings (Ta = 25°C)**

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	400	V	
Gate-source voltage	$V_{GSS}$	±30	V	
Drain current	Continuous	$I_D$ *4	±8	A
	Pulsed	$I_{DP}$	±32 *1 ±48 *2	A
Source current (Body Diode)	Continuous	$I_S$ *4	8	A
	Pulsed	$I_{SP}$	32 *1 48 *2	A
Avalanche current	$I_{AS}$ *3	4	A	
Avalanche energy	$E_{AS}$ *3	4.3	mJ	
Power dissipation	$P_D$ *5	20	W	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

\*2  $P_w \leq 1 \mu s$ , Duty cycle  $\leq 1\%$  Limited by Safe Operating Area. ( $V_{DS} \leq 30V$ )

\*3  $L = 500 \mu H$ ,  $V_{DD} = 50V$ ,  $R_G = 25 \Omega$ ,  $T_{ch} = 25^\circ C$

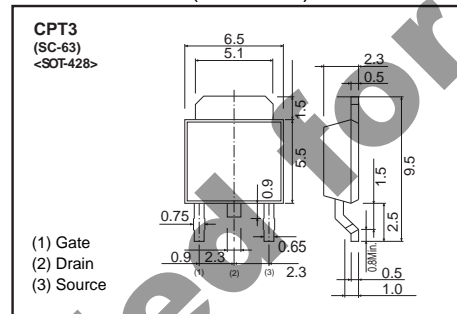
\*4 Limited only by maximum temperature allowed.

\*5  $T_C = 25^\circ C$

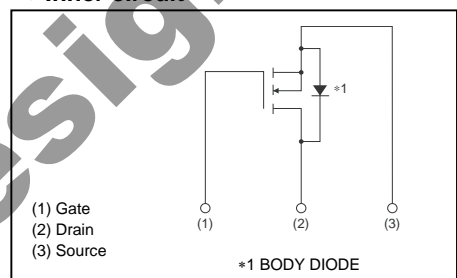
● **Thermal resistance**

Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th(ch-c)}$	6.25	°C / W

● **Dimensions (Unit : mm)**



● **Inner circuit**



**● Electrical characteristics (Ta = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±100	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	400	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	100	μA	$V_{DS}=400V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	2.5	-	4.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	0.73	0.95	Ω	$I_D=4A, V_{GS}=10V$
Forward transfer admittance	$ Y_{fs} ^*$	2	-	-	S	$V_{DS}=10V, I_D=4A$
Input capacitance	$C_{iss}$	-	500	-	pF	$V_{DS}=25V$
Output capacitance	$C_{oss}$	-	280	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	25	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	20	-	ns	$V_{DD}=200V, I_D=4A$
Rise time	$t_r^*$	-	20	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	48	-	ns	$R_L=50\Omega$
Fall time	$t_f^*$	-	16	-	ns	$R_G=10\Omega$
Total gate charge	$Q_g^*$	-	15	-	nC	$V_{DD}=200V$
Gate-source charge	$Q_{gs}^*$	-	3.5	-	nC	$I_D=8A$
Gate-drain charge	$Q_{gd}^*$	-	7	-	nC	$V_{GS}=10V$

\*Pulsed

**● Body diode characteristics (Source-Drain)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	1.5	V	$I_S=8A, V_{GS}=0V$

\*Pulsed

●Electrical characteristic curves

Fig.1 Maximum Safe Operating Area

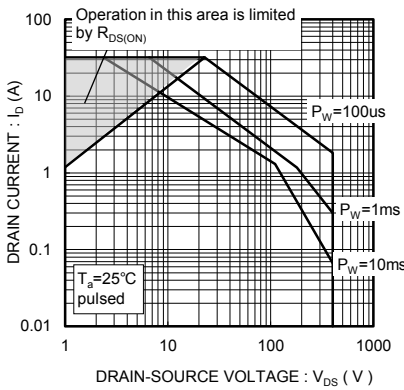


Fig.2 Typical Output Characteristics ( I )

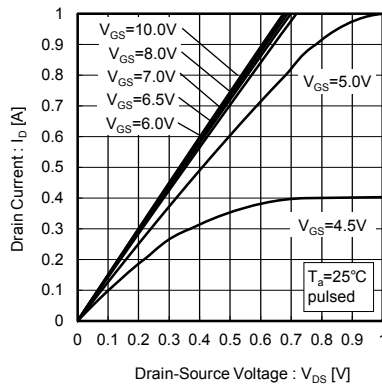


Fig.3 Typical Output Characteristics ( II )

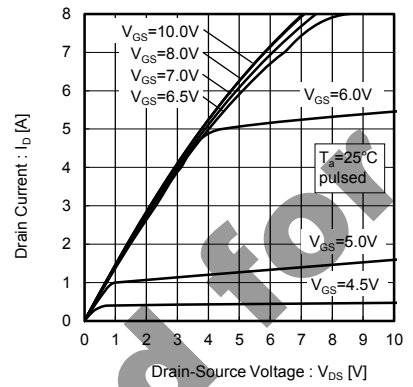


Fig.4 Typical Transfer Characteristics

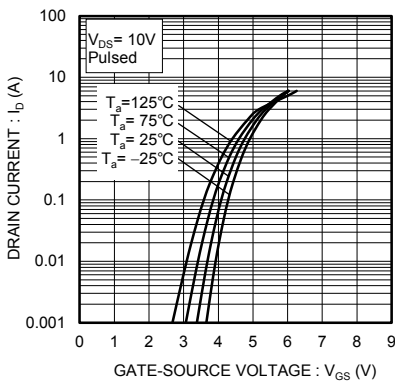


Fig.5 Gate Threshold Voltage vs. Channel Temperature

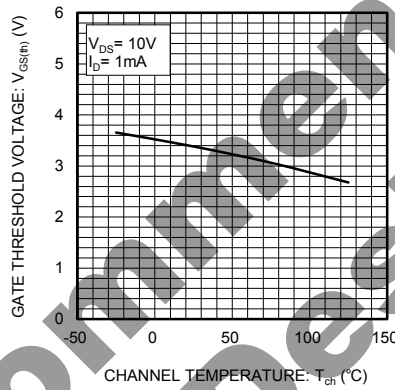


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

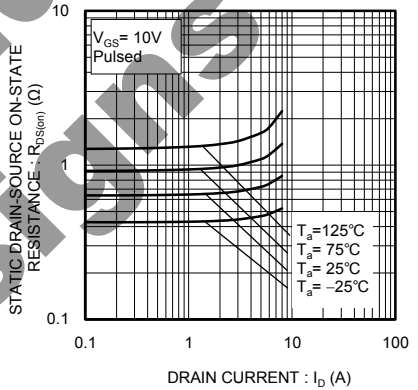


Fig.7 Static Drain-Source On-State Resistance vs. Gate Source Voltage

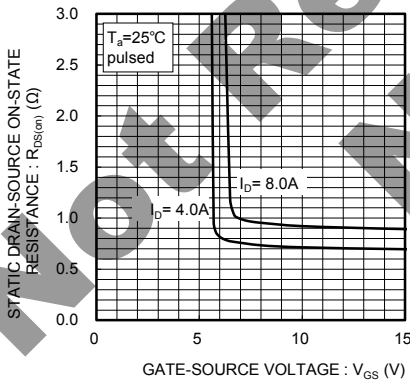


Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature

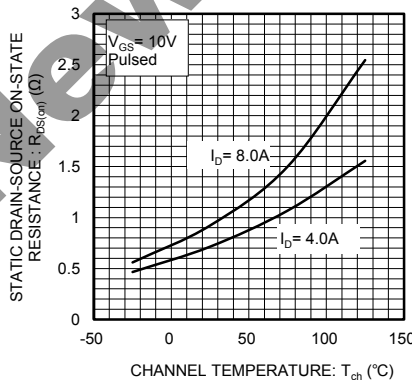


Fig.9 Forward Transfer Admittance vs. Drain Current

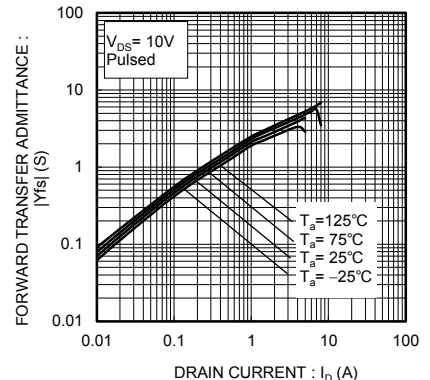


Fig.10 Reverse Drain Current vs. Source-Drain Voltage

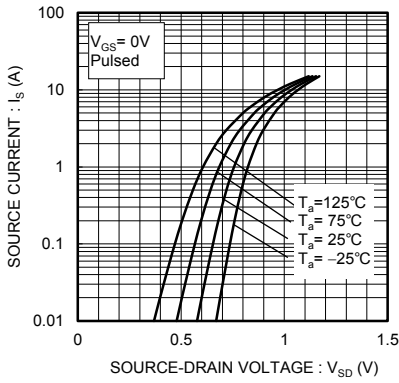


Fig.11 Typical Capacitance vs. Drain-Source Voltage

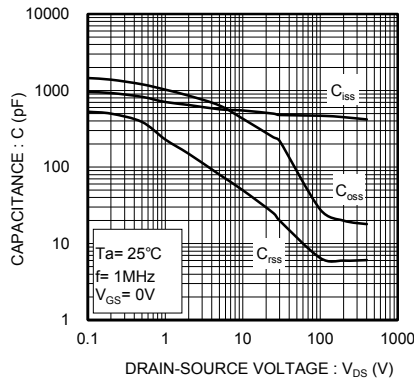


Fig.12 Dynamic Input Characteristics

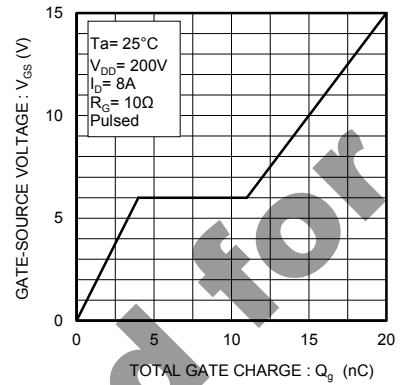


Fig.13 Reverse Recovery Time vs. Source Current

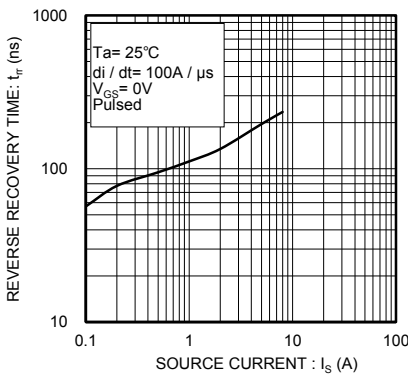


Fig.14 Switching Characteristics

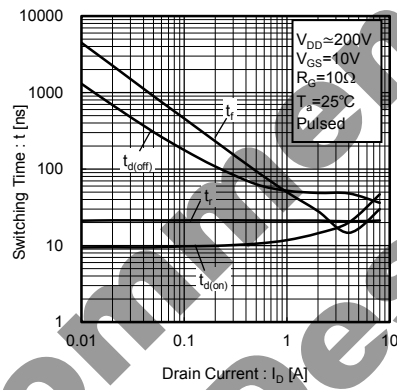
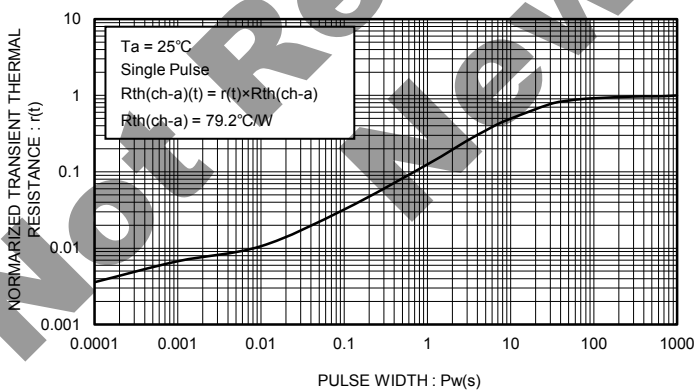


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width



● Measurement circuits

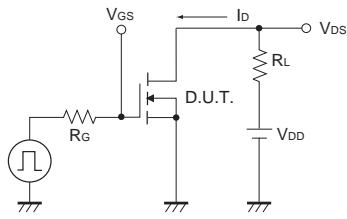


Fig.1-1 Switching Time Measurement Circuit

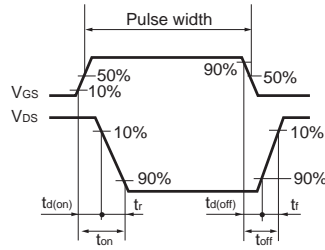


Fig.1-2 Switching Waveforms

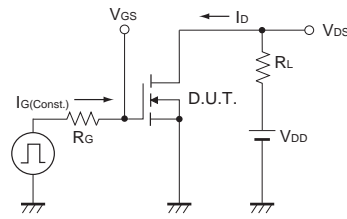


Fig.2-1 Gate Charge Measurement Circuit

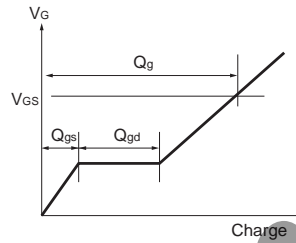


Fig.2-2 Gate Charge Waveform

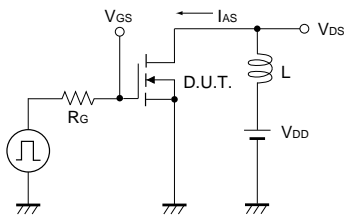


Fig.3-1 Avalanche Measurement Circuit

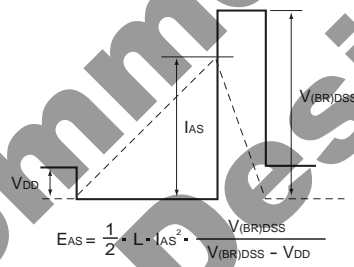


Fig.3-2 Avalanche Waveform

Not Recommended for New Designs

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